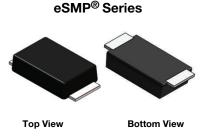
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# VS-3EYH01HM3, VS-3EYH02HM3

**Vishay Semiconductors** 



## Hyperfast Rectifier, 3 A FRED Pt®



#### SlimSMAW (DO-221AD)

Cathode Anode

O

#### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	3 A				
V <sub>R</sub>	100 V, 200 V				
V <sub>F</sub> at I <sub>F</sub>	0.71 V				
I <sub>FSM</sub>	70 A				
t <sub>rr</sub> (typ.)	16 ns				
T <sub>J</sub> max.	175 °C				
Package	SlimSMAW (DO-221AD)				
Circuit configuration	Single				

#### FEATURES

- Low profile package
- Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, class 2 whisker test
- Compatible to SOD-128 package case outline
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial, and automotive applications.

#### **MECHANICAL DATA**

**Case:** SlimSMAW (DO-221AD) Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

**Terminals:** matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage			100	V			
VS-3EYH02HM3	V <sub>RRM</sub>		200	v			
Average rectified forward current	I <sub>F(AV)</sub> <sup>(1)</sup>	T <sub>C</sub> = 137 °C	3	A			
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_J = 25 \ ^{\circ}C$ , 10 ms sine pulse wave	70				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			

#### Note

<sup>(1)</sup> Mounted on infinite heatsink

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking	VS-3EYH01HM3	V <sub>BR</sub> , V <sub>R</sub>	- I <sub>B</sub> = 100 μA	100	-	-	v	
voltage	VS-3EYH02HM3		$I_R = 100 \mu A$	200	-	-		
Forward voltage, per diode		V <sub>F</sub>	I <sub>F</sub> = 3 A	-	0.86	0.95		
			I <sub>F</sub> = 3 A, T <sub>J</sub> = 150 °C	-	0.71	0.79		
Reverse leakage current, per diode		I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	2		
			$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	20	μA	
Junction capacitance		CT	V <sub>R</sub> = 200 V	-	16	-	pF	

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1

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RoHS COMPLIANT HALOGEN

FREE

AUTOMOTIVE

# VS-3EYH01HM3, VS-3EYH02HM3



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/μs, V <sub>R</sub> = 30 V	-	22	-	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	100 A/ $\mu$ s, V <sub>R</sub> = 30 V	-	16	-	
Reverse recovery time	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, I_R = 1 \text{A}, I_{rr} = 0.25 \text{ A}$		-	-	30	ns
		T <sub>J</sub> = 25 °C		-	18	-	-
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 3 A, dI <sub>F</sub> /dt = 200 A/µs, V <sub>R</sub> = 100 V	-	30	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.5	-	A nC
reak recovery current		T <sub>J</sub> = 125 °C		-	4	-	
Bayaraa raaayany aharaa	0	T <sub>J</sub> = 25 °C		-	23	-	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	60	-	

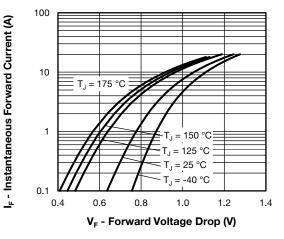
THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage	temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C	
Thermal resistance, junction to mount		R <sub>thJM</sub> <sup>(1)</sup>	Infinite heatsink	-	12	15		
Thermal resistance, junction to ambient		R <sub>thJA</sub>	Device mounted on FR4 PCB, 2 oz. standard footprint	-	120	150	°C/W	
VS-3EYH01HM3					3H1			
Marking device	VS-3EYH02HM3		Case style SlimSMAW (DO-221AD)	3H2				

Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC<sup>®</sup> 51-14 transient dual interface test method (TDIM)



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Fig. 1 - Typical Forward Voltage Drop Characteristics

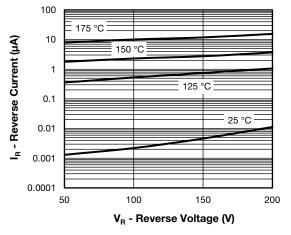


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

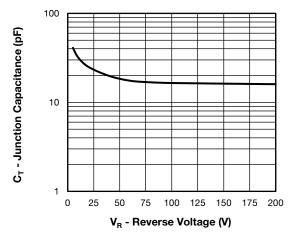


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

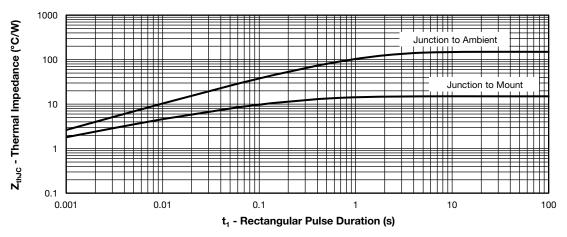
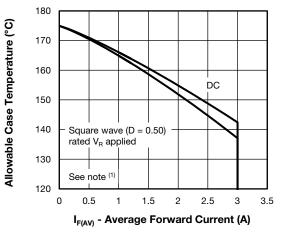


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

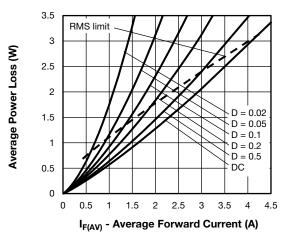


Fig. 6 - Forward Power Loss Characteristics

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV}$  = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

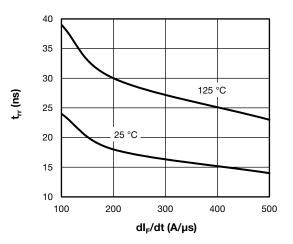


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

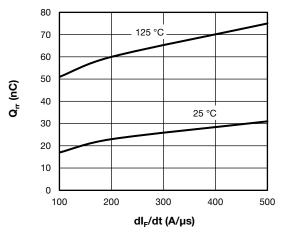


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

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## VS-3EYH01HM3, VS-3EYH02HM3

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#### **ORDERING INFORMATION TABLE**

Device code	vs-	3	Е	Y	н	02	Н	М3
	1	2	3	4	5	6	7	8
	1 · 2 ·		•	niconduo ng (3 = 3		oduct		
	3 -		uit conf single c	iguratior	ו:			
	4 -		•	IAW (DC	D-221AI	D)		
	5 -		cess typ	-				
	6 - 7 -	Volt	age coo	ist recov de (02 = 101 qua	200 V)			
	8 -			en-free,		complia	nt, and	termina

ORDERING INFORMATION (Example)									
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-3EYH01HM3/H	0.033	Н	3500	7"diameter plastic tape and reel					
VS-3EYH01HM3/I	0.033	I	14 000	13"diameter plastic tape and reel					
VS-3EYH02HM3/H	0.033	Н	3500	7"diameter plastic tape and reel					
VS-3EYH02HM3/I	0.033	1	14 000	13"diameter plastic tape and reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96582				
Part marking information	www.vishay.com/doc?95562				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96586				



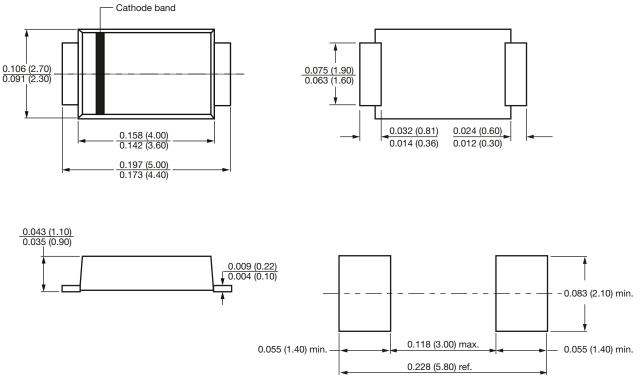
## **Outline Dimensions**

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## SlimSMAW (DO-221AD)

#### **DIMENSIONS** in inches (millimeters)

SlimSMAW (DO-221AD)



Mounting pad layout





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